

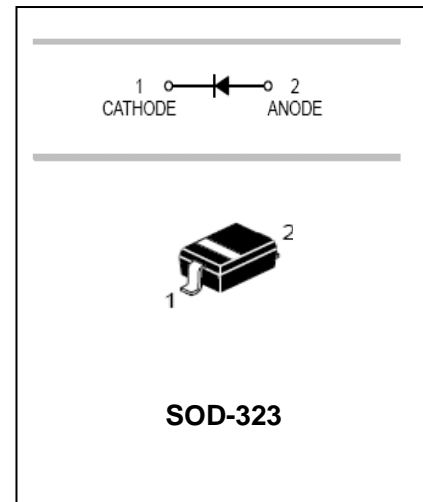
Schottky Barrier Diode

FEATURES

- High reliability
- Low voltage; Low inductance
- Low V_F

APPLICATIONS

- Low current rectification.



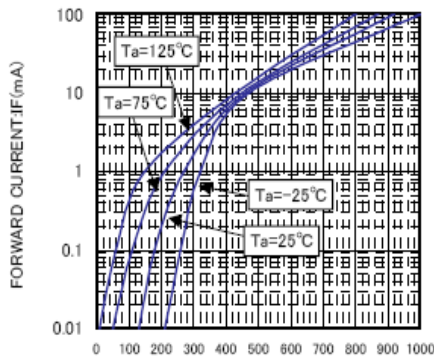
MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	30	V
Mean rectifying current	I_O	30	mA
Peak forward surge current	I_{FSM}	200	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +125	$^\circ\text{C}$

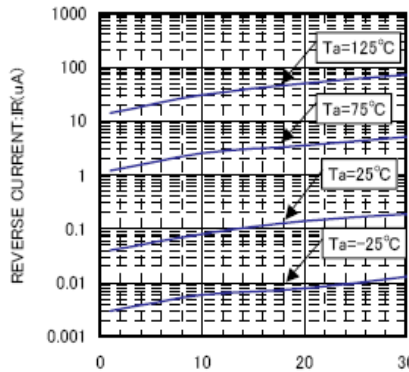
ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F			0.37	V	$I_F=1\text{mA}$
Reverse current	I_R			0.5	μA	$V_R=30\text{V}$
Capacitance between terminals	C_T		2		pF	$V_R=1\text{V}, f=1\text{MHz}$

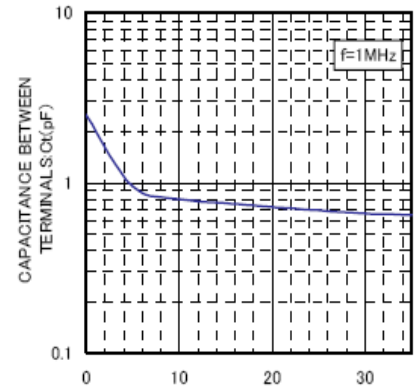
TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



FORWARD VOLTAGE: VF(mV)
VF-IF CHARACTERISTICS



REVERSE VOLTAGE: VR(V)
VR-IR CHARACTERISTICS



REVERSE VOLTAGE VR(V)
VR-Ct CHARACTERISTICS

PACKAGE OUTLINE

Plastic surface mounted package

SOD-323

SOD-323		
Dim	Min	Max
A	1.60	1.80
B	1.20	1.40
C	0.9 Typical	
D	0.30 Typical	
E	0.22	0.42
H	0.02	0.1
J	0.1 Typical	
K	2.55	2.75
All Dimensions in mm		